	L Number	Hits	Search Text	DB	Time stamp
	4	1138	134/113 134/104.1	USPAT	2003/09/05 14:41
	5	21	(134/113 134/104.1) and (dress\$3 grind\$3	USPAT	2003/09/05 14:41
	١	2.	condition\$3 clean\$3) near5 (pad cloth	002711	2000,00,00 21.12
			platen)		
	_	274	156/345.12 156/345.13 156/345.16	USPAT	2003/09/04 10:29
, V		13915		USPAT	2003/09/04 10:29
	_	13913	condition\$3)	USFAI	2003/09/04 10:30
		1270		USPAT	2003/09/04 10:32
	_	12/0	("chemical mechanical" adj(polishing	USPAT	2003/09/04 10:32
			planariz\$5) same (grind\$3 condition\$3))	II O D M M	2003/09/04 10:34
	_	U	(("chemical mechanical" adj(polishing	USPAT	2003/09/04 10:34
	1		planariz\$5) same (grind\$3 condition\$3)))		
L	i /		<pre>same ((analyz\$3 monitor\$3) adj3 (slurry</pre>		
	1	10	solution))	110070	2003/09/04 10:42
an	- /	10	(("chemical mechanical" adj(polishing	USPAT	2003/09/04 10:42
1	/		planariz\$5) same (grind\$3 condition\$3)))		
dan			<pre>same ((analyz\$3 monitor\$3) same (slurry</pre>		-
art seat no 09/97		2547	solution))		0000 (00 (04 10 40
No		3517	· · · · · · · · · · · · · · · · · · ·	USPAT	2003/09/04 10:48
00/07	3,204		(cu copper)		0000 (00 (0
04[4]	21-	559	(("ammonium citrate" "nitric acid") same	USPAT	2003/09/04 10:49
	1		(cu copper)) and (polish\$3 abrad\$3		
	*		planariz\$5)		
	- 1		chopra-dinesh.in. meikle-scott.in.	USPAT	2003/09/04 12:59
	- 1	1111	micron.as. and (condition\$3 dress\$3) and	USPAT	2003/09/04 13:00
	\		(analy\$4 monitor\$3)		
	- \	261	micron.as. and (condition\$3 dress\$3) same	USPAT	2003/09/04 14:10
			(analy\$4 monitor\$3)		
		3.05_	_(polish\$3,abrad\$3) same (gas air) same	USPAT	2003/09/04 14:12
		_ !	(Spring)	**** * ****	
	_	2	("chemical mechanical" adj (polish\$3	USPAT	2003/09/04 14:32
1			abrad33) same (gas air) same (spring)		
	7	2422	("chemikal mechanical" adj (polish\$3	USPAT	2003/09/04 14:17
100	,		abrad\$3)) same (dry plasma)		
, -	_	70	(("chemical mechanical" adj (polish\$3	USPAT	2003/09/04 14:17
01 N	1		abrad(3)) same (dry plasma)) and (spring		
4 5	107		or "pressure releasing")		
7	γ- J	3598	((dry plasma) same (polish\$3 abrad\$3	EPO; JPO;	2003/09/04 14:33
			planari\$5))	DERWENT	
	-	654	((dry plasma) adj5 polish\$3 abrad\$3	EPO; JPO;	2003/09/04 14:33
			planari\$5))	DERWENT	
		143	((dry plasma) adj5 (palish\$3 abrad\$3	EPO; JPO;	2003/09/04 14:50
			planari\$5))) and (wafer semiconductor)	DERWENT	
	_	11	(√(dry plasma) adj5 (polish\$3 abrad\$3	USPAT;	2003/09/04 14:51
			planari\$5))) and (wafer sericonductor) and	EPO; JPO;	
			(spring pressure)	DERWENT	